

annular configuration around the transistors of the coupling circuit, but is limited to two islands, each of which is conductively connected to one of the two potentials V_{ss1} , V_{ss2} .

Since it is possible to keep the doping concentration relatively low in the shielding doping zone 23, its conductivity may be maintained at a low value similar to that of the substrate 13.

Although the present invention has been shown and described with respect to several preferred embodiments thereof, various changes, omissions and additions to the form and detail thereof, may be made therein, without departing from the spirit and scope of the invention.

What is claimed is: